

Patent Abstracts of Japan

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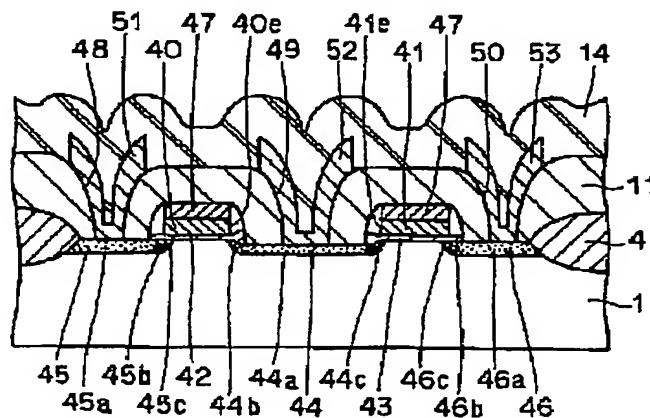
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H01L 27/088

TITLE : MANUFACTURE OF
SEMICONDUCTOR DEVICE



ABSTRACT : PURPOSE: To obtain a semiconductor device in which no parasitic gate overlap capacitance appear on the drain side of a MOS transistor.

CONSTITUTION: First and second gate electrodes 40 and 41 are provided on a semiconductor substrate 1. A common drain electrode 44 is provided in the main surface of the silicon substrate 1 and between the first and second gate electrodes 40 and 41. The common drain region 44 contains a high-concentration impurity region 44a and a pair of low-concentration impurity regions 44b and 44c. The peripheries of the low-concentration impurity regions 44b and 44c are on the same planes as the side wall surface of the gate electrodes 40 and 41.

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